

FGS15N40L

General Description

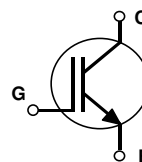
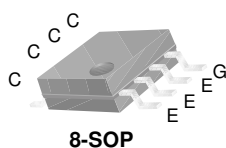
Insulated Gate Bipolar Transistors(IGBTs) with trench gate structure have superior performance in conduction and switching to planar gate structure and also have wide noise immunity. These devices are well suitable for strobe application

Features

- High Input Impedance
- High Peak Current Capability (130A)
- Easy Gate Drive

Application

- Strobe Flash



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description	FGS15N40L	Units
V _{CES}	Collector-Emitter Voltage	400	V
V _{GES}	Gate-Emitter Voltage	± 6	V
I _{CM (1)}	Pulsed Collector Current	130	A
P _C	Maximum Power Dissipation @ T _a = 25°C	2.0	W
T _J	Operating Junction Temperature	-40 to +150	°C
T _{stg}	Storage Temperature Range	-40 to +150	°C
T _L	Maximum Lead Temp. for soldering Purposes from case for 5 secnds	300	°C

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
R _{θJA}	Thermal Resistance, Junction-to-Ambient(PCB Mount)	--	62.5	°C/W

Notes: Mounted on 1" square PCB(FR4 or G-10 Material)

Electrical Characteristics of IGBT $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	450	--	--	V
I_{CES}	Collector Cut-off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	10	μA
I_{GES}	G-E leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	± 0.1	μA
On Characteristics						
$V_{GE(th)}$	G-E threshold Voltage	$I_C = 0V, I_C = 1mA$	-	-	1.4	V
$V_{CE(sat)}$	C-E Saturation Voltage	$I_C = 130A, V_{GE} = 4.0V$	2.0	4.5	8.0	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{GE} = 0V, V_{CE} = 30V$ $f = 1MHz$	--	3800	--	pF
C_{oes}	Output Capacitance		--	45	--	pF
C_{res}	Reverse Transfer Capacitance		--	30	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 130A$ $V_{GE} = 4.0V, R_G = 15\Omega *$ Resistive Load	--	0.15	--	us
t_r	Rise Time		--	1.5	--	us
$t_{d(off)}$	Turn-Off Delay Time		--	0.15	0.3	us
t_f	Fall Time		--	1.5	3.0	us

Notes : Recommendation of Rg Value : $R_g \geq 15\Omega$

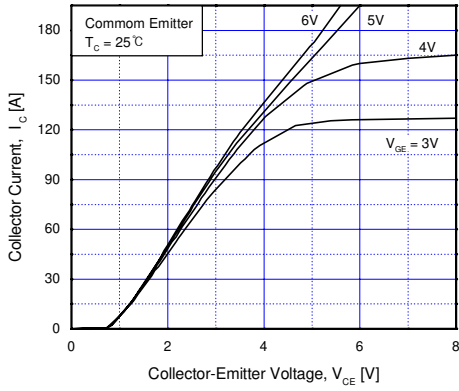


Fig 1. Typical Output Characteristics

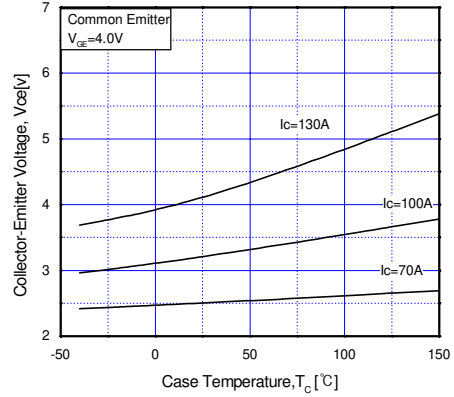


Fig 2. Saturation Voltage vs. Case Temperature at Variant Current Level

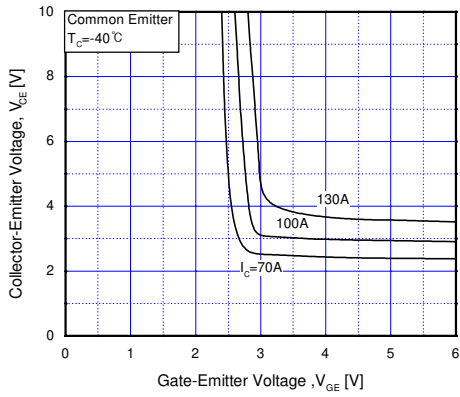


Fig 3. Saturation Voltage vs. V_{GE}

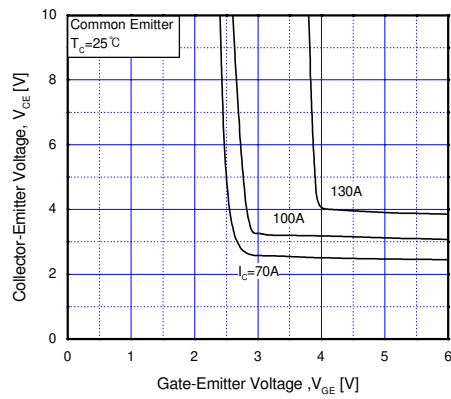


Fig 4. Saturation Voltage vs. V_{GE}

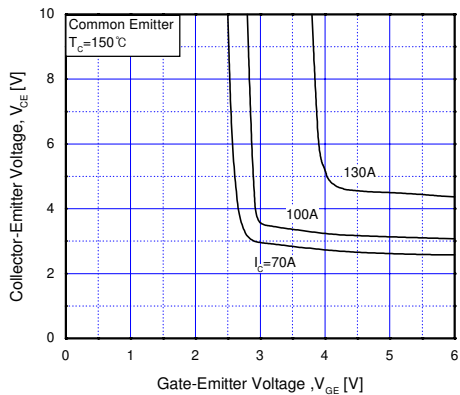


Fig 5. Saturation Voltage vs. V_{GE}

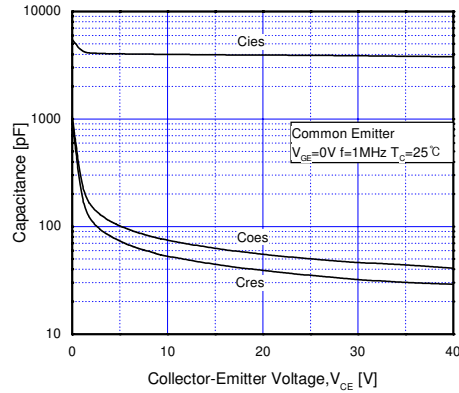


Fig 6. Capacitance Characteristics

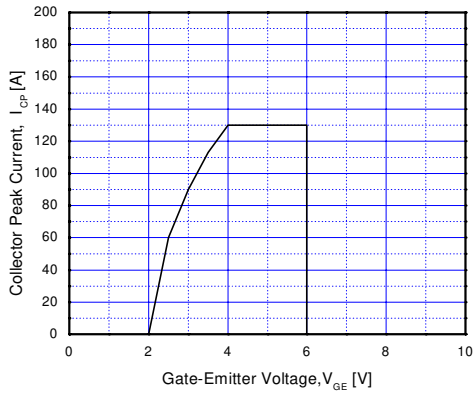
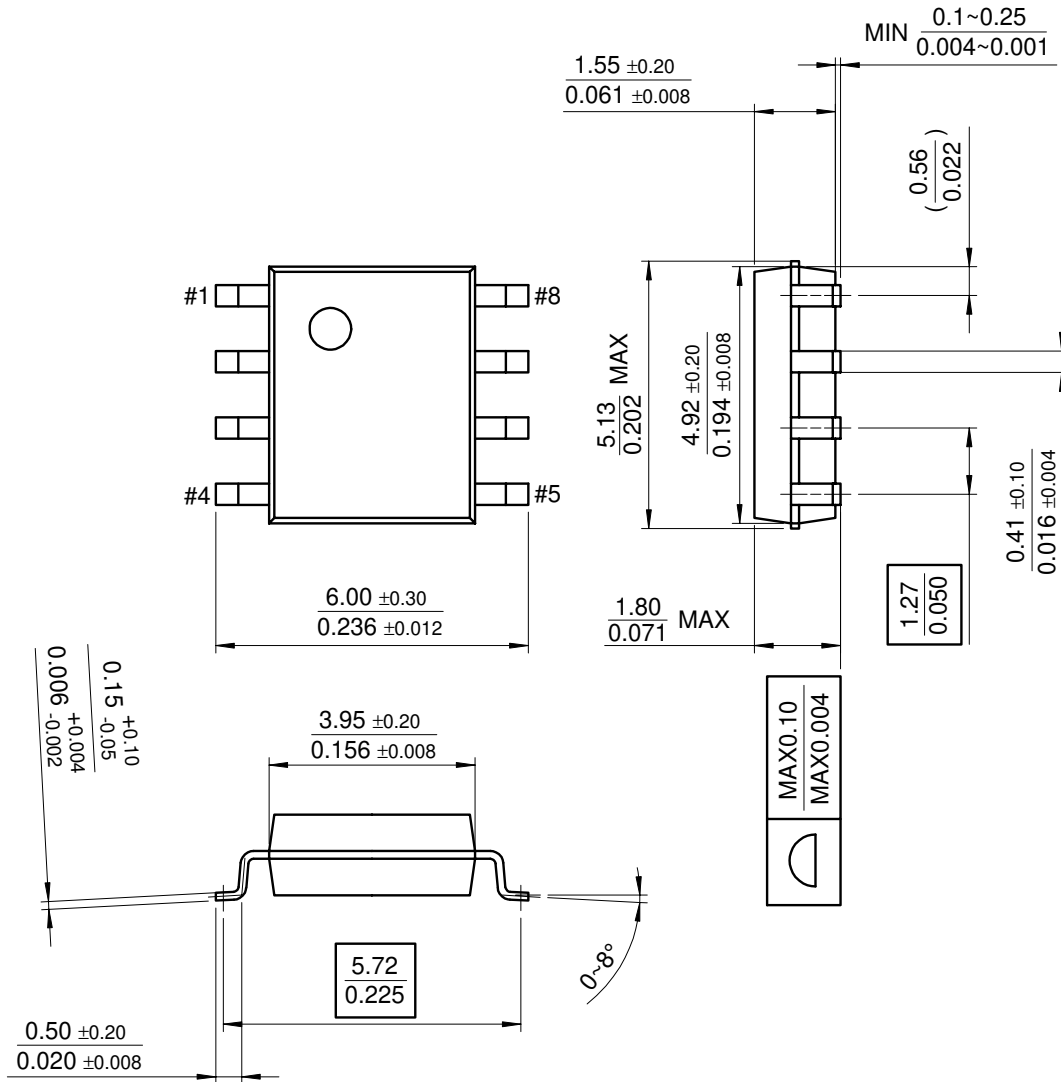


Fig 7. Collector Current Limit Vs Gate - Emitter Voltage Limit

Package Dimension

FGS15N40L

8-SOP



Dimensions in Millimeters

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FGS15N40L
Discrete, IGBT

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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
FGS15N40LTF	Full Production	\$1.36	SOIC	8	TAPE REEL
FGS15N40LTU	Full Production	\$1.36	SOIC	8	RAIL

* 1,000 piece Budgetary Pricing

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